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December 2013

# FQP8N80C / FQPF8N80C / FQPF8N80CYDTU

# N-Channel QFET® MOSFET

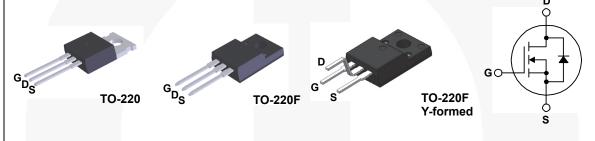
800 V, 8.0 A, 1.55 Ω

# **Description**

This N-Channel enhancement mode power MOSFET is • 8.0 A, 800 V,  $R_{DS(on)}$  = 1.55  $\Omega$  (Max.) @  $V_{GS}$  = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 35 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 13 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

### **Features**

- $I_D = 4.0 A$



# Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP8N80C	FQPF8N80C	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		8	00	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		8	8 *	Α	
	- Continuous (T <sub>C</sub> = 100°C)		5.1	5.1 *	Α	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	32	32 *	Α	
V <sub>GSS</sub>	Gate-Source Voltage		± 30		V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy		850		mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	8		Α	
E <sub>AR</sub>	Repetitive Avalanche Energy (N		17.8		mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5		V/ns	
$P_{D}$	Power Dissipation (T <sub>C</sub> = 25°C)		178	59	W	
	- Derate above 25°C		1.43	0.48	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to	+150	°C	
T <sub>L</sub>	Maximum lead temperature for soldering,		300		°C	
.r	1/8" from case for 5 seconds		3	J0 C		

<sup>\*</sup> Drain current limited by maximum junction temperature.

### **Thermal Characteristics**

Symbol	Parameter	FQP8N80C	FQPF8N80C	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.89	2.66	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ, Max.	0.5		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W	

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP8N80C	FQP8N80C	TO-220	Tube	N/A	N/A	50 units
FQPF8N80C	FQPF8N80C	TO-220F	Tube	N/A	N/A	50 units
FQPF8N80CYDTU	FQPF8N80C	TO-220F (Y-formed)	Tube	N/A	N/A	50 units

# **Electrical Characteristics**

T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Uni
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	800			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 μA, Referenced to 25°C		0.5		V/°(
I <sub>DSS</sub> Zero Gate Voltage Drain Current	Zoro Coto Voltago Droin Current	V <sub>DS</sub> = 800 V, V <sub>GS</sub> = 0 V			10	μΑ
	V <sub>DS</sub> = 640 V, T <sub>C</sub> = 125°C			100	μΑ	
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nΑ
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4 A		1.29	1.55	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 4 A (Note 4)		5.6		S
	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		1580	2050	pF
Coss	Output Capacitance	f = 1.0 MHz		135	175	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			13	17	pF
Switchi	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 400 V, I <sub>D</sub> = 8 A,		40	90	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		110	230	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			65	140	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4, 5)	/	70	150	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 640 V, I <sub>D</sub> = 8 A,	<i>/</i> -	35	45	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V		10		nC
		(Note 4, 5)		14		nC

# $Q_{rr}$

 $I_{SM}$ 

 $V_{\text{SD}}$ 

 $t_{rr}$ 

Notes: 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 25 mH, I<sub>AS</sub> = 8 A, V<sub>DD</sub> = 50 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  8 A, di/dt  $\leq$  200 A/ $\mu$ s, V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4. Pulse test : pulse-width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%. 5. Essentially independent of operating temperature.

Drain-Source Diode Forward Voltage

**Drain-Source Diode Characteristics and Maximum Ratings** Maximum Continuous Drain-Source Diode Forward Current

Maximum Pulsed Drain-Source Diode Forward Current

Reverse Recovery Time

Reverse Recovery Charge

8

32

1.4

690

8.2

(Note 4)

Α

Α

٧

ns

μС

 $V_{GS}$  = 0 V,  $I_{S}$  = 8 A

 $V_{GS} = 0 V, I_{S} = 8 A,$ 

 $dI_F / dt = 100 A/\mu s$ 

# **Typical Characteristics**

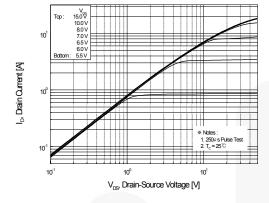


Figure 1. On-Region Characteristics

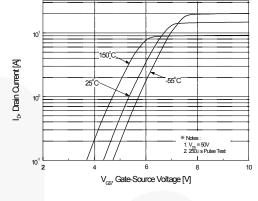


Figure 2. Transfer Characteristics

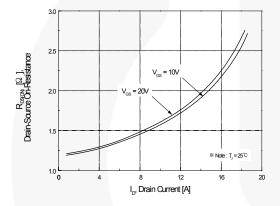


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

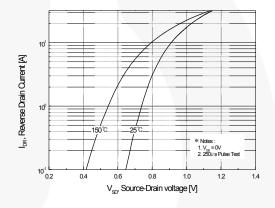


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

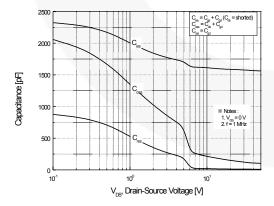


Figure 5. Capacitance Characteristics

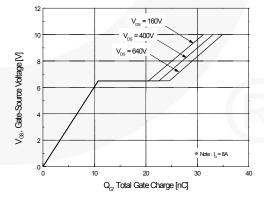


Figure 6. Gate Charge Characteristics

# Typical Characteristics (Continued)

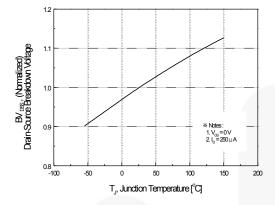


Figure 7. Breakdown Voltage Variation vs Temperature

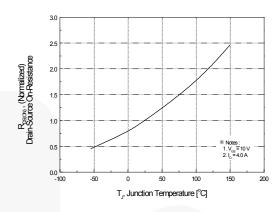


Figure 8. On-Resistance Variation vs Temperature

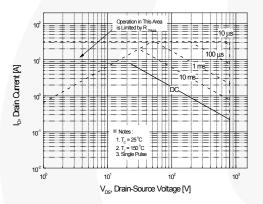


Figure 9-1. Maximum Safe Operating Area for FQP8N80C

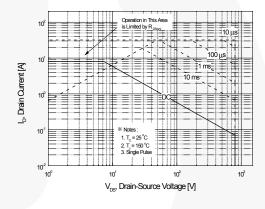


Figure 9-2. Maximum Safe Operating Area for FQPF8N80C

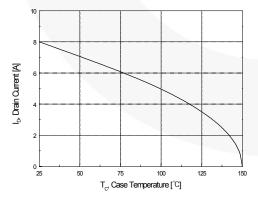


Figure 10. Maximum Drain Current vs Case Temperature

# Typical Characteristics (Continued)

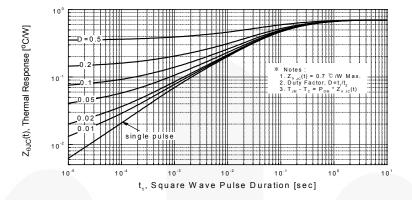


Figure 11-1. Transient Thermal Response Curve for FQP8N80C

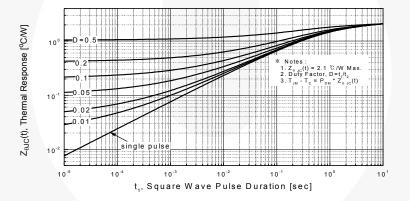


Figure 11-2. Transient Thermal Response Curve for FQPF8N80C

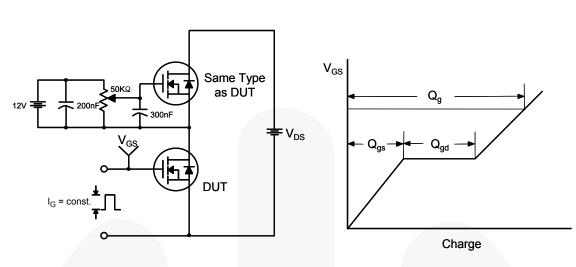


Figure 12. Gate Charge Test Circuit & Waveform

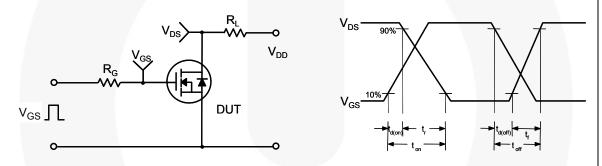


Figure 13. Resistive Switching Test Circuit & Waveforms

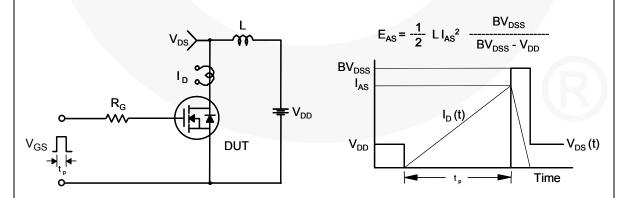
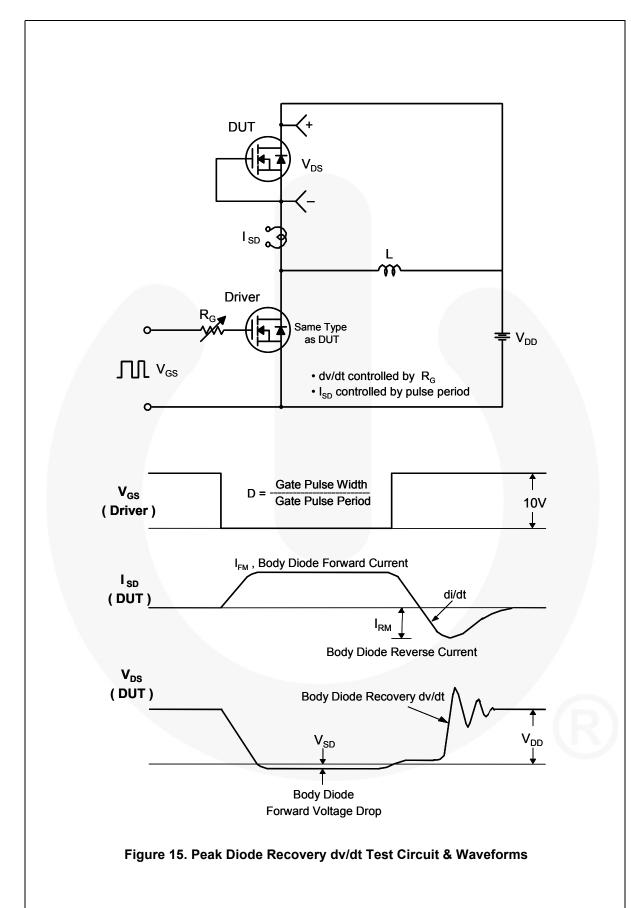


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**

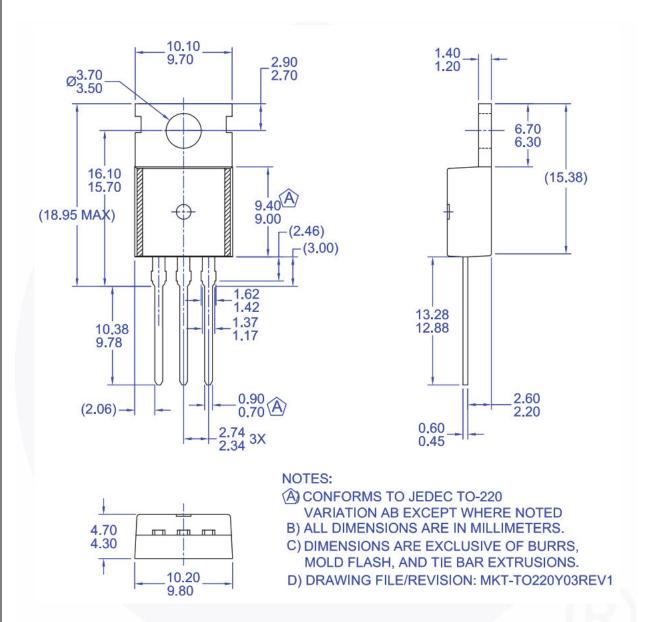


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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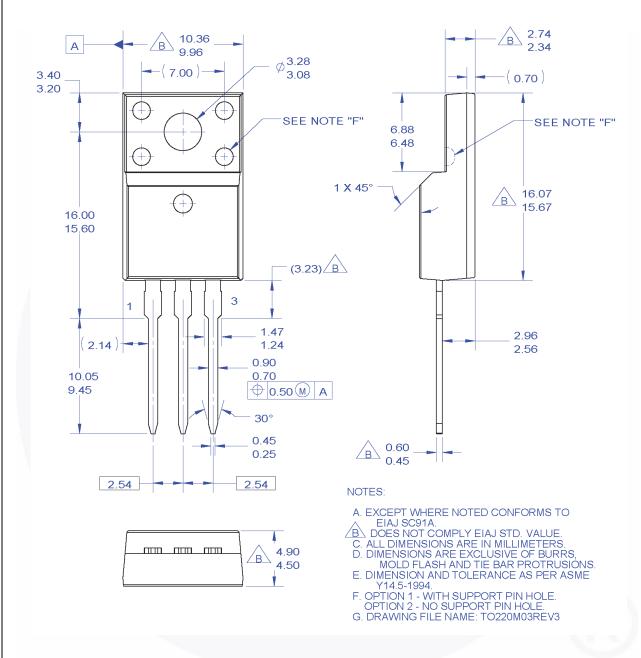


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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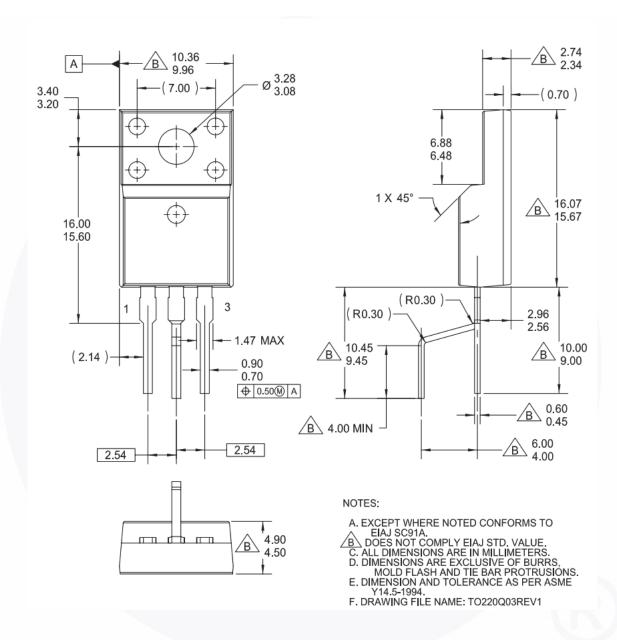


Figure 18. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Y-Formed

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